

Triacs logic level

BT136X series D

GENERAL DESCRIPTION

Glass passivated, sensitive gate triacs in a full pack plastic envelope, intended for use in general purpose bidirectional switching and phase control applications. These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

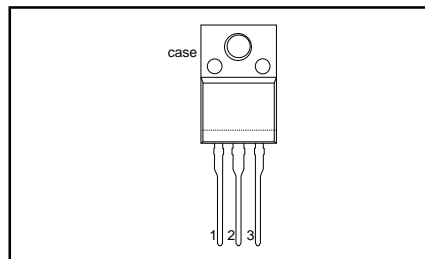
QUICK REFERENCE DATA

| SYMBOL | PARAMETER | MAX. | MAX. | UNIT |
|--------------|--|--------------------|--------------------|------|
| V_{DRM} | BT136X- Repetitive peak off-state voltages RMS on-state current Non-repetitive peak on-state current | 500D 500 | 600D 600 | V |
| $I_{T(RMS)}$ | | 4 | 4 | A |
| I_{TSM} | | 25 | 25 | A |

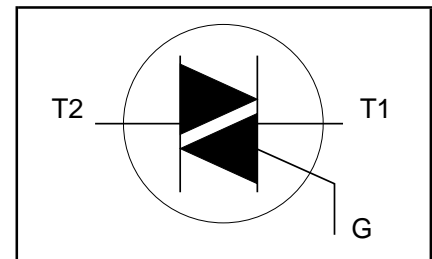
PINNING - SOT186A

| PIN | DESCRIPTION |
|------|-----------------|
| 1 | main terminal 1 |
| 2 | main terminal 2 |
| 3 | gate |
| case | isolated |

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | | UNIT |
|--------------|--|---|------|--------------------------|--------------------------|------------------|
| | | | | -500 500 ¹ | -600 600 ¹ | |
| V_{DRM} | Repetitive peak off-state voltages | | - | | | V |
| $I_{T(RMS)}$ | RMS on-state current | full sine wave; $T_{hs} \leq 92^\circ\text{C}$ | - | 4 | | A |
| I_{TSM} | Non-repetitive peak on-state current | full sine wave; $T_j = 125^\circ\text{C}$ prior to surge; with reapplied $V_{DRM(max)}$ $t = 20\text{ ms}$ | - | 25 | | A |
| | | $t = 16.7\text{ ms}$ | - | 27 | | A |
| | | $t = 10\text{ ms}$ | - | 3.1 | | A ² s |
| I^2t | I^2t for fusing | | - | | | |
| di_T/dt | Repetitive rate of rise of on-state current after triggering | $I_{TM} = 6\text{ A}$; $I_G = 0.2\text{ A}$; $di_G/dt = 0.2\text{ A}/\mu\text{s}$ | | | | |
| | | T2+ G+ | - | 50 | | A/ μs |
| | | T2+ G- | - | 50 | | A/ μs |
| | | T2- G- | - | 50 | | A/ μs |
| | | T2- G+ | - | 10 | | A/ μs |
| I_{GM} | Peak gate current | | - | 2 | | A |
| V_{GM} | Peak gate voltage | | - | 5 | | V |
| P_{GM} | Peak gate power | | - | 5 | | W |
| $P_{G(AV)}$ | Average gate power | over any 20 ms period | - | 0.5 | | W |
| T_{stg} | Storage temperature | | -40 | 150 | | $^\circ\text{C}$ |
| T_j | Operating junction temperature | | - | 125 | | $^\circ\text{C}$ |

¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 3 A/ μs .

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ISOLATION LIMITING VALUE & CHARACTERISTIC

$T_{hs} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|------------|--|--|------|------|------|------|
| V_{isol} | R.M.S. isolation voltage from all three terminals to external heatsink | $f = 50\text{-}60\text{ Hz}$; sinusoidal waveform; $R.H. \leq 65\%$; clean and dustfree | - | | 2500 | V |
| C_{isol} | Capacitance from T2 to external heatsink | $f = 1\text{ MHz}$ | - | 10 | - | pF |

THERMAL RESISTANCES

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-----------------------|---|---|------|------|------|------|
| $R_{th\ j\text{-}hs}$ | Thermal resistance junction to heatsink | full or half cycle with heatsink compound | - | - | 5.5 | K/W |
| $R_{th\ j\text{-}a}$ | Thermal resistance junction to ambient | without heatsink compound in free air | - | 55 | 7.2 | K/W |

STATIC CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise stated

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|----------|---------------------------|---|------|------|------|------|
| I_{GT} | Gate trigger current | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$ | | | | |
| | | T2+ G+ | - | 2.0 | 5 | mA |
| | | T2+ G- | - | 2.5 | 5 | mA |
| | | T2- G- | - | 2.5 | 5 | mA |
| I_L | Latching current | $V_D = 12\text{ V}$; $I_{GT} = 0.1\text{ A}$ | | | | |
| | | T2- G+ | - | 5.0 | 10 | mA |
| | | T2+ G+ | - | 1.6 | 10 | mA |
| | | T2+ G- | - | 4.5 | 15 | mA |
| I_H | Holding current | $V_D = 12\text{ V}$; $I_{GT} = 0.1\text{ A}$ | | | | |
| | | T2- G- | - | 1.2 | 10 | mA |
| | | T2- G+ | - | 2.2 | 15 | mA |
| | | T2+ G+ | - | 1.2 | 10 | mA |
| V_T | On-state voltage | $I_T = 5\text{ A}$ | - | 1.4 | 1.70 | V |
| V_{GT} | Gate trigger voltage | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$ | - | 0.7 | 1.5 | V |
| I_D | Off-state leakage current | $V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 125\text{ }^{\circ}\text{C}$ | 0.25 | 0.4 | - | V |
| | | $V_D = V_{DRM(max)}$; $T_j = 125\text{ }^{\circ}\text{C}$ | - | 0.1 | 0.5 | mA |

DYNAMIC CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise stated

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-----------|--|--|------|------|------|------------------|
| dV_D/dt | Critical rate of rise of off-state voltage | $V_{DM} = 67\% V_{DRM(max)}$; $T_j = 125\text{ }^{\circ}\text{C}$; exponential waveform; $R_{GK} = 1\text{ k}\Omega$ | - | 5 | - | V/ μs |
| t_{gt} | Gate controlled turn-on time | $I_{TM} = 6\text{ A}$; $V_D = V_{DRM(max)}$; $I_G = 0.1\text{ A}$; $di_G/dt = 5\text{ A}/\mu\text{s}$ | - | 2 | - | μs |

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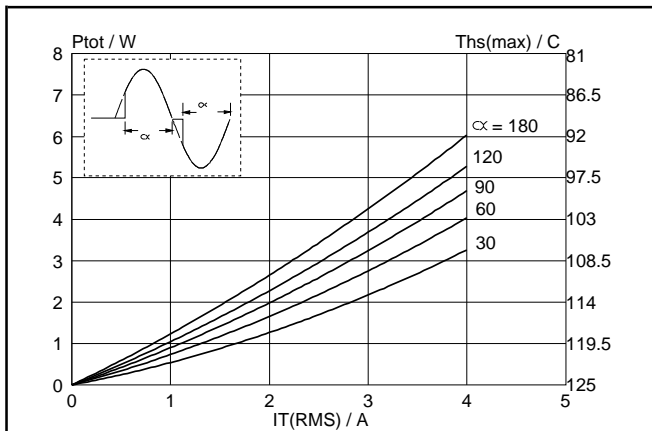


Fig.1. Maximum on-state dissipation, P_{tot} , versus rms on-state current, $I_{T(RMS)}$, where $\alpha =$ conduction angle.

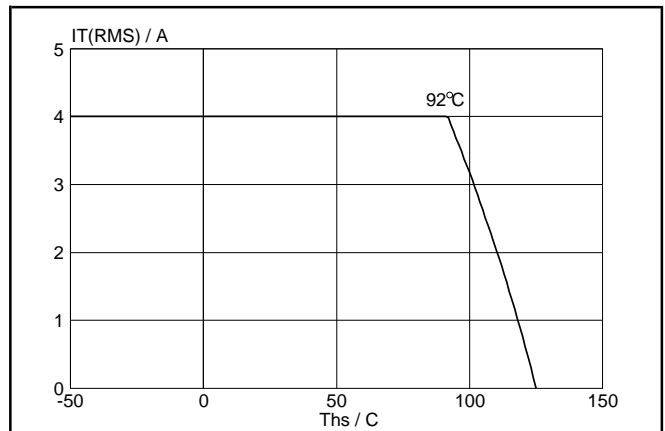


Fig.4. Maximum permissible rms current $I_{T(RMS)}$, versus heatsink temperature T_{hs} .

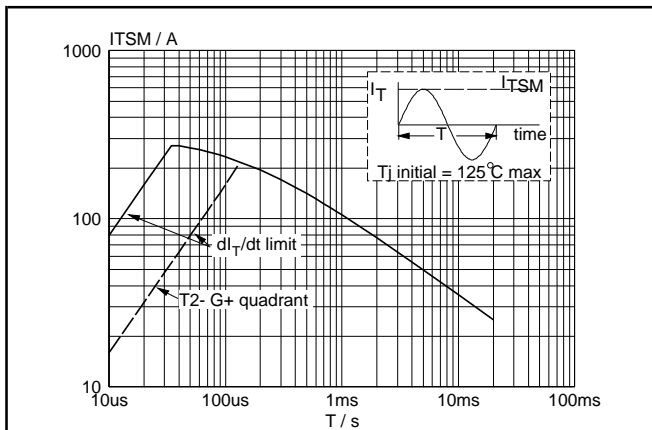


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \leq 20\text{ms}$.

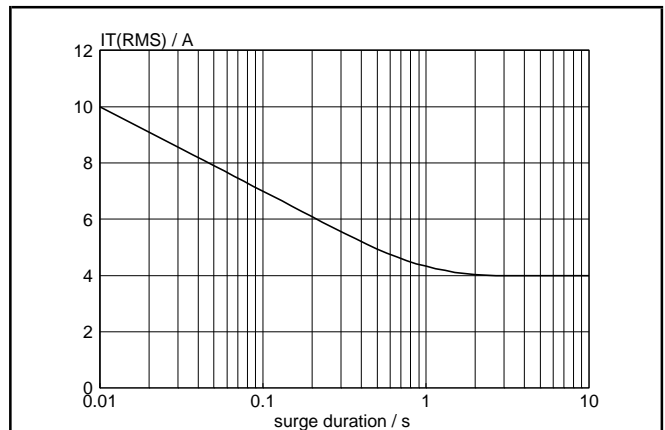


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, $f = 50\text{ Hz}$; $T_{hs} \leq 92^\circ\text{C}$.

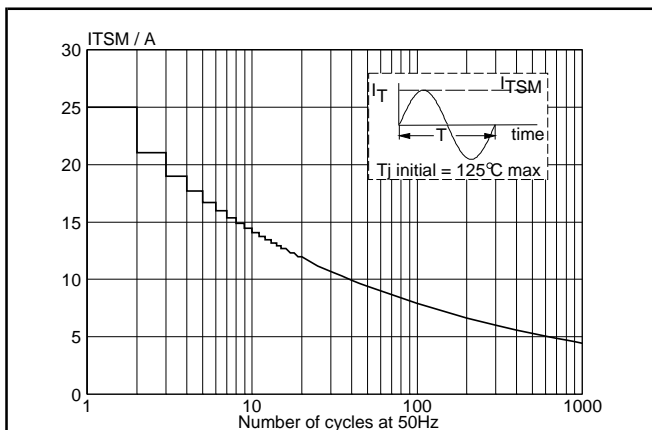


Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, $f = 50\text{ Hz}$.

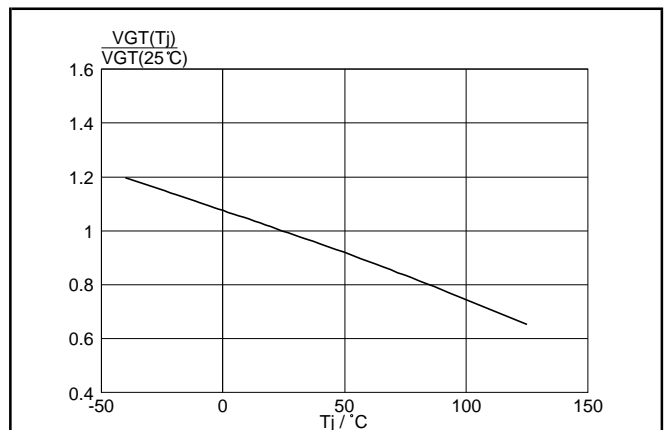
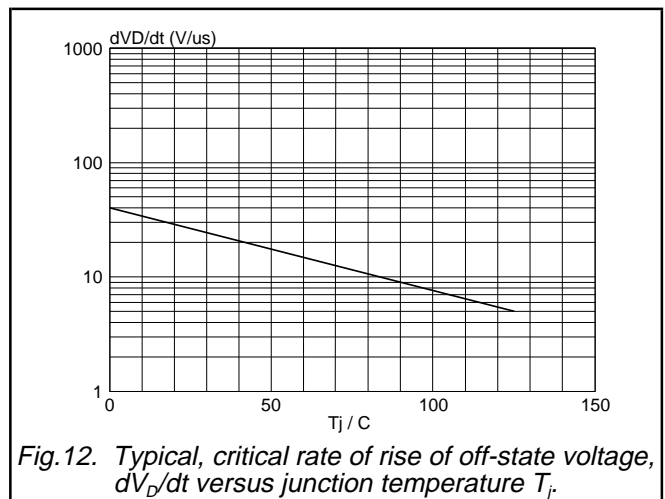
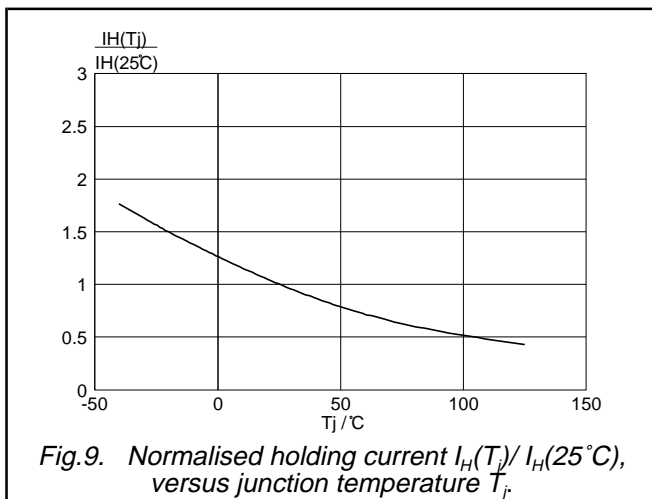
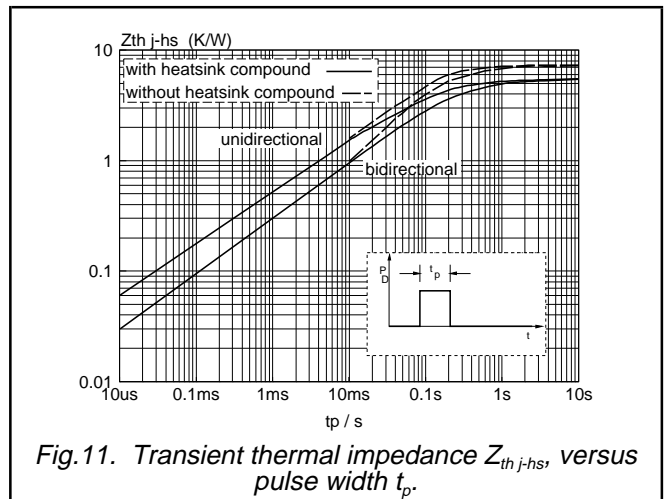
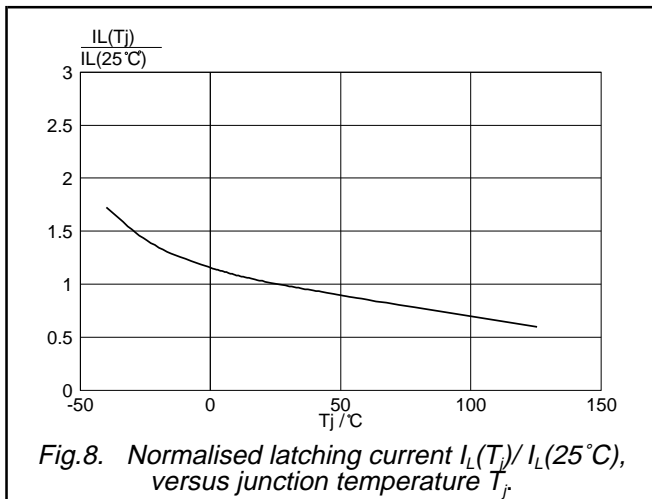
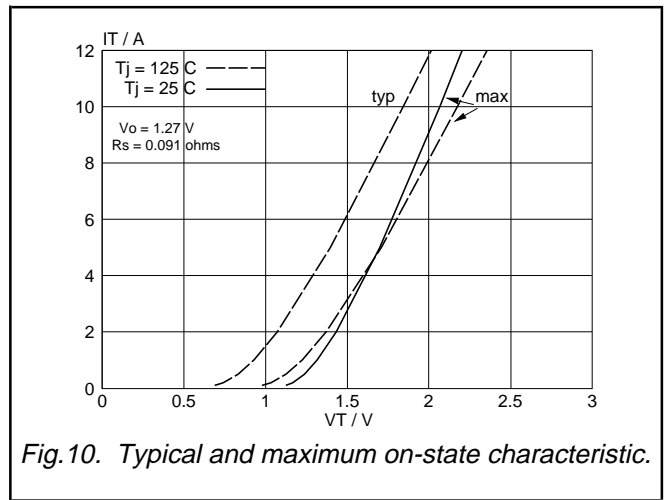
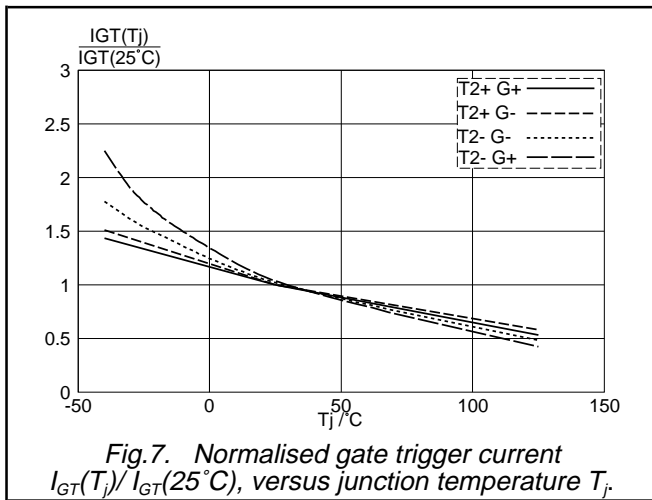


Fig.6. Normalised gate trigger voltage $V_{GT}(T_j) / V_{GT}(25^\circ\text{C})$, versus junction temperature T_j .

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MECHANICAL DATA

Dimensions in mm

Net Mass: 2 g

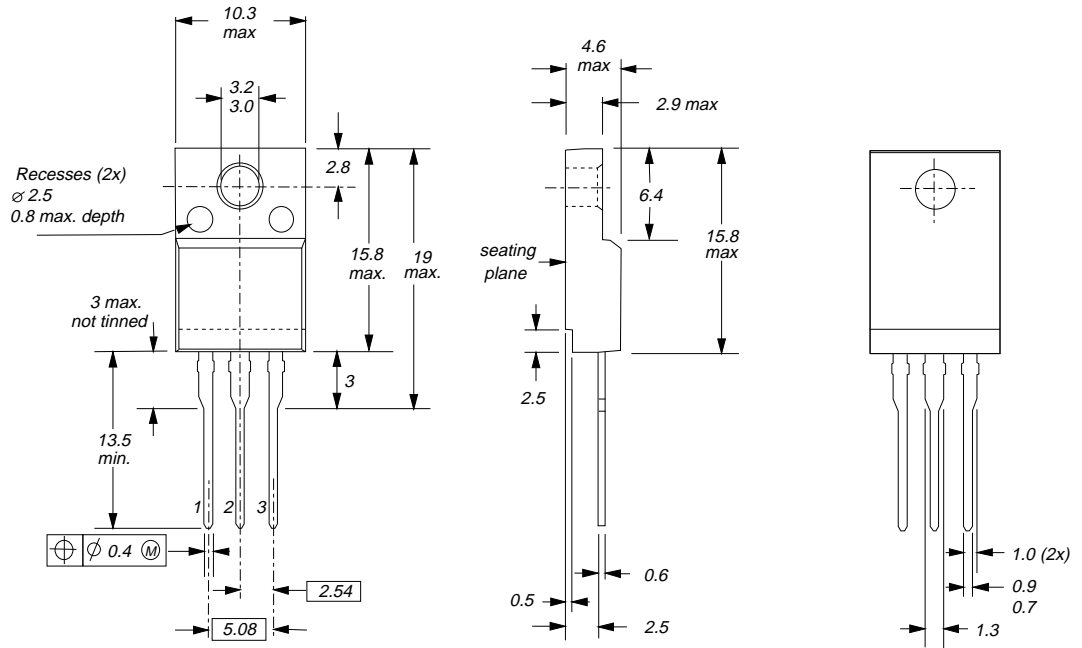


Fig. 13. SOT186A; The seating plane is electrically isolated from all terminals.

Notes

1. Accessories supplied on request: refer to mounting instructions for F-pack envelopes.
2. The improved isolation rating applies only to the SOT186 version A envelope.

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DEFINITIONS

| | |
|--|---|
| Data sheet status | |
| Objective specification | This data sheet contains target or goal specifications for product development. |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification | This data sheet contains final product specifications. |
| Limiting values | |
| Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability. | |
| Application information | |
| Where application information is given, it is advisory and does not form part of the specification. | |
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